

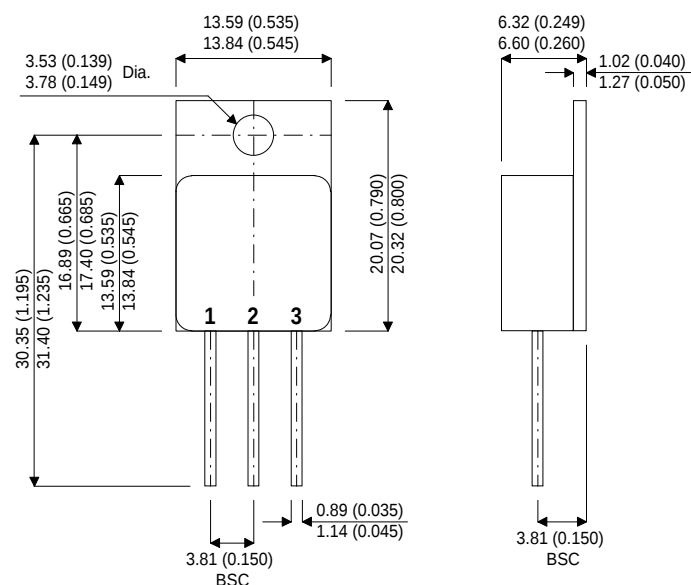
TO-254 Package Outline.

Dimensions in mm (inches)

**N-CHANNEL
ENHANCEMENT MODE
HIGH VOLTAGE
POWER MOSFETS**

V_{DSS} **500V**
 $I_{D(cont)}$ **15A**
 $R_{DS(on)}$ **0.270Ω**

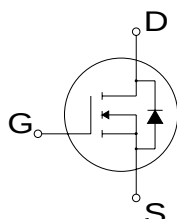
- **Faster Switching**
- **Lower Leakage**
- **100% Avalanche Tested**
- **TO-254 Hermetic Package**



Pin 1 – Drain

Pin 2 – Source

Pin 3 – Gate



StarMOS is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimises the JFET effect, increases packing density and reduces the on-resistance. StarMOS also achieves faster switching speeds through optimised gate layout.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	500	V
I_D	Continuous Drain Current	15	A
I_{DM}	Pulsed Drain Current ¹	60	A
V_{GS}	Gate – Source Voltage	±30	V
V_{GSM}	Gate – Source Voltage Transient	±40	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	140	W
	Derate Linearly	2	W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to 150	°C
T_L	Lead Temperature : 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ¹ (Repetitive and Non-Repetitive)	20	A
E_{AR}	Repetitive Avalanche Energy ¹	30	mJ
E_{AS}	Single Pulse Avalanche Energy ⁴	960	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

 4) Starting $T_J = 25^{\circ}C$, $L = 4.8mH$, $R_G = 25\Omega$, Peak $I_L = 20A$

STATIC ELECTRICAL RATINGS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0V$)	$V_{DS} = V_{DSS}$			25	μA
		$V_{DS} = 0.8V_{DSS}, T_C = 125^{\circ}\text{C}$			250	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1.0mA$	2		4	V
$I_{D(ON)}$	On State Drain Current ²	$V_{DS} > I_{D(ON)} \times R_{DS(ON)} \text{ Max}$ $V_{GS} = 10V$	15			A
$R_{DS(ON)}$	Drain – Source On State Resistance ²	$V_{GS} = 10V, I_D = 0.5 I_D [\text{Cont.}]$			0.27	Ω

DYNAMIC CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		2600	3180	pF
C_{oss}	Output Capacitance			360	500	
C_{rss}	Reverse Transfer Capacitance			150	225	
Q_g	Total Gate Charge ³	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^{\circ}\text{C}$		110	175	nC
Q_{gs}	Gate – Source Charge			19	30	
Q_{gd}	Gate – Drain (“Miller”) Charge			45	70	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D [\text{Cont.}] @ 25^{\circ}\text{C}$ $R_G = 1.6\Omega$		10	20	ns
t_r	Rise Time			11	22	
$t_{d(off)}$	Turn-off Delay Time			43	70	
t_f	Fall Time			7	14	

SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	(Body Diode)			15	A
I_{SM}	Pulsed Source Current ¹	(Body Diode)			60	
V_{SD}	Diode Forward Voltage ²	$V_{GS} = 0V, I_S = -I_D [\text{Cont.}]$			1.3	V
t_{rr}	Reverse Recovery Time	$I_S = -I_D [\text{Cont.}], dI_S / dt = 100A/\mu s$		410		ns
Q_{rr}	Reverse Recovery Charge	$I_S = -I_D [\text{Cont.}], dI_S / dt = 100A/\mu s$		6.5		μC

THERMAL CHARACTERISTICS

	Characteristic	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction to Case			0.625	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Junction to Ambient			40	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width $< 380\mu s$, Duty Cycle $< 2\%$

3) See MIL-STD-750 Method 3471



CAUTION — Electrostatic Sensitive Devices. Anti-Static Procedures Must Be Followed.